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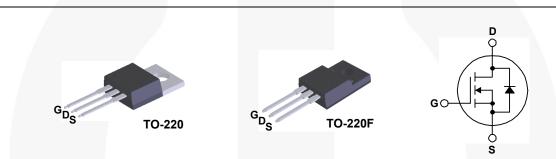
### FQP45N15V2 / FQPF45N15V2 N-Channel QFET<sup>®</sup> MOSFET 150 V, 45 A, 40 mΩ

#### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

#### Features

- 45 A, 150 V,  ${\sf R}_{{\sf DS}({\sf on})}$  = 40 m $\Omega$  (Max.) @ V\_{{\sf GS}} = 10 V,  ${\sf I}_{\sf D}$  = 22.5 A
- Low Gate Charge (Typ. 72 nC)
- Low Crss (Typ. 135 pF)
- 100% Avalanche Tested



#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

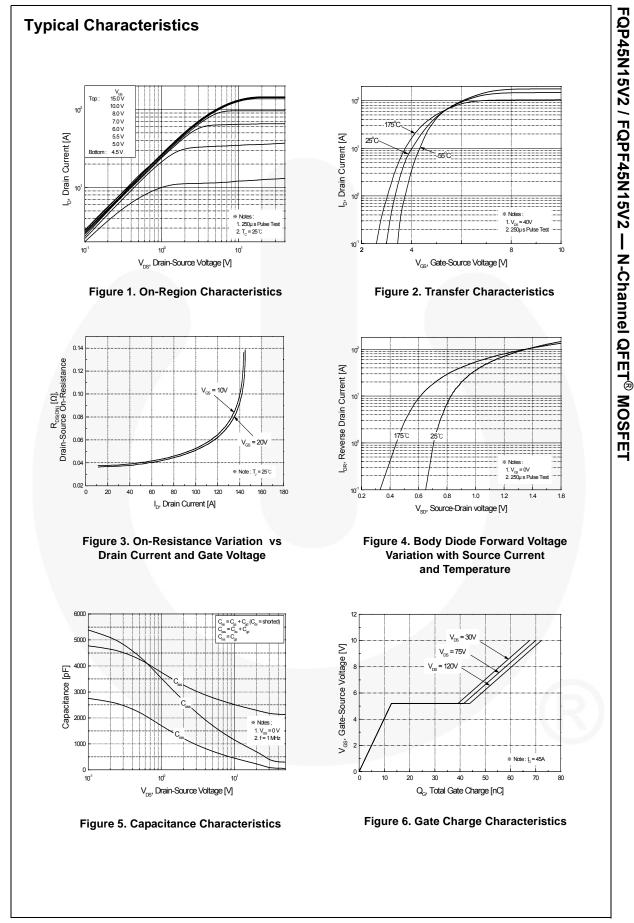
Symbol	Parameter		FQP45N15V2	FQPF45N15V2	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		1	V		
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^{\circ}C$ )	1	45	45 *	А	
	- Continuous (T <sub>C</sub> = 100°C	))	31	31 *	А	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	180	180 *	А	
V <sub>GSS</sub>	Gate-Source Voltage		±	30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	11	1124		
I <sub>AR</sub>	Avalanche Current	(Note 1)	4	45		
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)		2	mJ		
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4	V/ns		
PD	Power Dissipation (T <sub>C</sub> = 25°C)		220	66	W	
	- Derate above 25°C		1.47	0.44	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to	°C		
TL	Maximum lead temperature for soldering purposes,		3	°C		
۰L	1/8" from case for 5 seconds	5				

Drain current innited by maximum junction temperatur

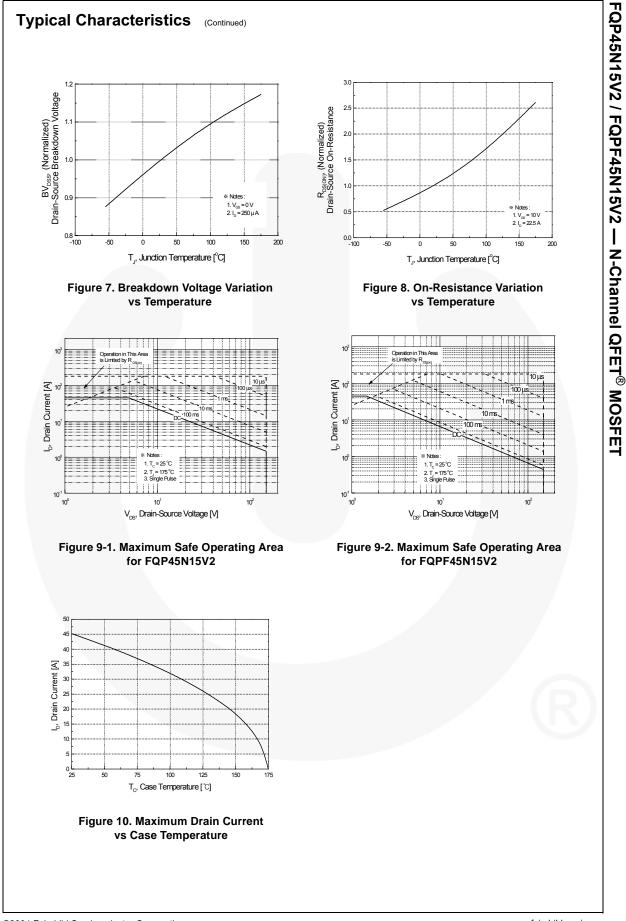
#### **Thermal Characteristics**

Symbol	Parameter	FQP45N15V2	FQPF45N15V2	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.68	2.25	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.5		°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W

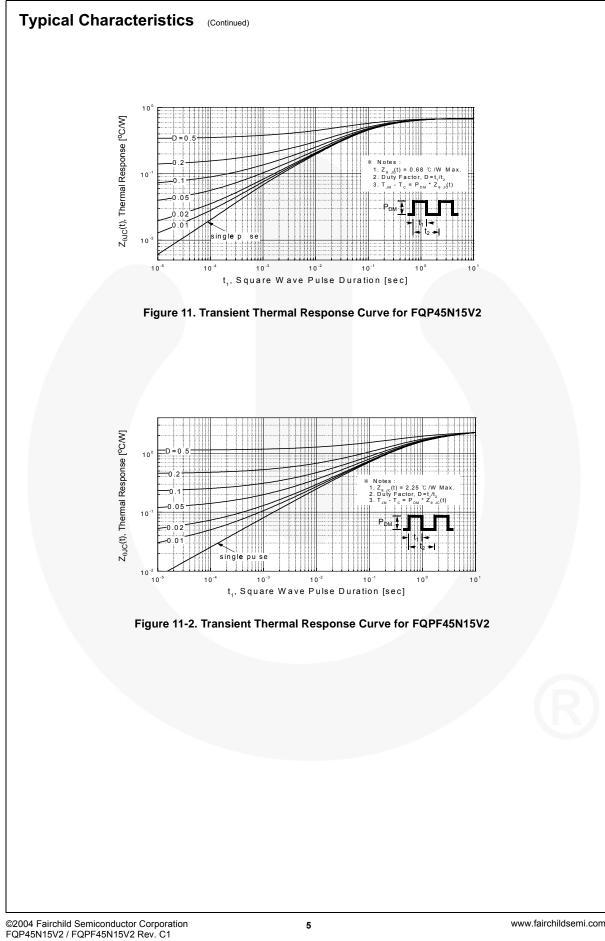
FQP45N	mber	Top Mark Pack				leel S	Size	Tape Width N/A		Quantity 50 units
	P45N15V2 PV245N15 T		TO-220			N/A	4			
FQPF45	N15V2	FQPF45N15V2	TO-220F	Tube		N/A	A	N/A		50 units
Electri Symbol	cal Cl	haracteristics	$\Gamma_c = 25^{\circ}C$ unless oth	erwise noted. Test Conditions	2		Min	Тур	Max	Unit
					5			iyp	max	Unit
Off Cha BV <sub>DSS</sub>		T <b>istics</b> Source Breakdown Volta		<sub>s</sub> = 0 V, I <sub>D</sub> = 250 μA			150			V
∆BV <sub>DSS</sub>				ς – ο ν, η – 200 μλ			150			v
$\Delta \Delta V_{\rm DSS}$	Coeffic	down Voltage Temperati sient	- D	250 μA, Referenced	l to 25	°C		0.21		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current		nt	$V_{DS} = 150 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 120 \text{ V}, T_{C} = 150^{\circ}\text{C}$					1 10	μA μA
GSSF	Gate-F	Body Leakage Current, I		s = 30 V, V <sub>DS</sub> = 0 V					100	nA
I <sub>GSSR</sub>		Body Leakage Current, I		$_{\rm S} = -30$ V, V <sub>DS</sub> = 0 V					-100	nA
On Cha	racter	istics								
V <sub>GS(th)</sub>		hreshold Voltage	V <sub>DS</sub>	<sub>s</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA			2.0		4.0	V
R <sub>DS(on)</sub>		Drain-Source sistance	V <sub>Gs</sub>	<sub>s</sub> = 10 V, I <sub>D</sub> = 22.5 A				0.034	0.04	Ω
9 <sub>FS</sub>	Forwar	rd Transconductance	V <sub>DS</sub>	s = 40 V, I <sub>D</sub> = 22.5 A				40		S
D	ia Cha	restariation								
uvnam	ic Una	racteristics								
	1	racteristics Capacitance	Vpc	$= 25 V V_{cs} = 0 V$				2330	3030	pF
C <sub>iss</sub>	Input C			<sub>5</sub> = 25 V, V <sub>GS</sub> = 0 V, 1.0 MHz				2330 510	3030 670	pF pF
C <sub>iss</sub> C <sub>oss</sub>	Input C Output	Capacitance	f = 1							
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input C Output Revers	Capacitance Capacitance se Transfer Capacitance	f = 1			-		510	670	pF
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> Switchi	Input C Output Revers	Capacitance Capacitance	f = -	1.0 MHz				510	670	pF
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> Switchi	Input C Output Revers ing Ch	Capacitance : Capacitance se Transfer Capacitance aracteristics	f =	1.0 MHz <sub>0</sub> = 75 V, I <sub>D</sub> = 45 A,				510 135	670 176	pF pF
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> Switchi t <sub>d(on)</sub> t <sub>r</sub>	Input C Output Revers ing Ch Turn-C Turn-C	Capacitance Capacitance Se Transfer Capacitance aracteristics On Delay Time	f =	1.0 MHz				510 135 22	670 176 54	pF pF ns
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> Switchi t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub>	Input C Output Revers ing Ch Turn-C Turn-C Turn-C	Capacitance Capacitance se Transfer Capacitance <b>aracteristics</b> On Delay Time On Rise Time	f =	1.0 MHz <sub>0</sub> = 75 V, I <sub>D</sub> = 45 A,	(Not	te 4)	  	510 135 22 232	670 176 54 474	pF pF ns ns
$\begin{array}{c} C_{iss} \\ C_{oss} \\ C_{rss} \\ \end{array}$	Input C Output Revers Turn-C Turn-C Turn-C Turn-C	Capacitance Capacitance Se Transfer Capacitance aracteristics On Delay Time On Rise Time Off Delay Time	f =	1.0 MHz <sub>0</sub> = 75 V, I <sub>D</sub> = 45 A, = 25 Ω	(Not	te 4)	  	510 135 22 232 224	670 176 54 474 458	pF pF ns ns ns
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> Switchi t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Q <sub>g</sub>	Input C Output Reverss ing Ch Turn-C Turn-C Turn-C Turn-C Turn-C	Capacitance Capacitance se Transfer Capacitance <b>aracteristics</b> On Delay Time On Rise Time Off Delay Time Off Fall Time	f =	1.0 MHz $p = 75 V, I_D = 45 A,$ $= 25 \Omega$ $q = 120 V, I_D = 45 A,$	(Not	te 4)	  	510 135 22 232 224 246	670 176 54 474 458 502	pF pF ns ns ns ns
$\frac{C_{iss}}{C_{oss}}$ $\frac{C_{rss}}{Switchi}$ $\frac{t_{d(on)}}{t_r}$ $\frac{t_{d(off)}}{t_f}$	Input C Output Reverss ing Ch Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C	Capacitance Capacitance Se Transfer Capacitance aracteristics On Delay Time On Rise Time Off Delay Time Off Fall Time Sate Charge	f =	1.0 MHz <sub>0</sub> = 75 V, I <sub>D</sub> = 45 A, = 25 Ω	(Not	-	     	510 135 22 232 224 246 72	670 176 54 474 458 502 94	pF pF ns ns ns ns nc
$C_{iss}$ $C_{oss}$ $C_{rss}$ <b>Switchi</b> $t_{d(on)}$ $t_{r}$ $t_{d(off)}$ $t_{f}$ $Q_{g}$ $Q_{gs}$ $Q_{gd}$	Input C Output Reverse ing Ch Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C	Capacitance Capacitance Se Transfer Capacitance aracteristics On Delay Time On Rise Time Off Delay Time Off Fall Time Sate Charge Source Charge Orain Charge	f = 1	1.0 MHz $_{D} = 75 \text{ V}, \text{ I}_{D} = 45 \text{ A},$ $= 25 \Omega$ $_{S} = 120 \text{ V}, \text{ I}_{D} = 45 \text{ A},$ $_{S} = 10 \text{ V}$	(Not	-	     	510 135 22 232 224 246 72 13	670 176 54 474 458 502 94	pF pF ns ns ns ns nC nC
$C_{iss}$ $C_{oss}$ $C_{rss}$ <b>Switchi</b> $t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$ $Q_g$ $Q_{gs}$ $Q_{gd}$ <b>Drain-S</b>	Input C Output Reverse ing Cha Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C Total G Gate-S Gate-E	Capacitance Capacitance Se Transfer Capacitance aracteristics On Delay Time On Rise Time Off Delay Time Off Fall Time Sate Charge Source Charge Orain Charge	f = 1	1.0 MHz $p = 75 V, I_{D} = 45 A,$ $= 25 \Omega$ $q = 120 V, I_{D} = 45 A,$ q = 10 V <b>laximum Rating</b>	(Not	-	     	510 135 22 232 224 246 72 13	670 176 54 474 458 502 94	pF pF ns ns ns nc nC
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> Switchi t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub> Drain-S I <sub>s</sub>	Input C Output Reverse ing Ch Turn-C	Capacitance Capacitance Se Transfer Capacitance aracteristics On Delay Time On Rise Time Off Delay Time Off Fall Time Sate Charge Source Charge Orain Charge	f =           VDE           RG           VDE           VGS           Stics and M           Fource Diode Fe	1.0 MHz $_{D} = 75 V, I_{D} = 45 A,$ $_{S} = 25 \Omega$ $_{S} = 120 V, I_{D} = 45 A,$ $_{S} = 10 V$ <b>laximum Rating</b> proward Current	(Not	-	           	510 135 22 232 224 246 72 13 31	670 176 54 474 458 502 94  	pF pF ns ns ns nc nC nC
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> Switchi t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub> Drain-S I <sub>S</sub>	Input C Output Reverse ing Ch Turn-C Turn-C Turn-C Turn-C Turn-C Turn-C Total G Gate-S Gate-S Gate-S Gate-S Gate-S Maxim	Capacitance Capacitance Se Transfer Capacitance aracteristics On Delay Time On Rise Time Off Delay Time Off Fall Time Sate Charge Source Charge Orain Charge Diode Characteri um Continuous Drain-S	f =           y           RG           VDE           VGE           VGE           Stics and M           ource Diode Forward	1.0 MHz $_{D} = 75 V, I_{D} = 45 A,$ $_{S} = 25 \Omega$ $_{S} = 120 V, I_{D} = 45 A,$ $_{S} = 10 V$ <b>laximum Rating</b> proward Current	(Not	-	          	510 135 22 232 224 246 72 13 31	670 176 54 474 458 502 94   45	PF pF ns ns ns nc nC nC nC
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> Switchi t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub> Drain-S I <sub>s</sub>	Input C Output Revers ing Ch Turn-C T	Capacitance Capacitance Se Transfer Capacitance aracteristics On Delay Time On Rise Time Off Delay Time Off Fall Time Gate Charge Orain Charge Diode Characteri um Continuous Drain-S um Pulsed Drain-Source	f = f	1.0 MHz $_{D} = 75 V, I_{D} = 45 A,$ $= 25 \Omega$ $_{3} = 120 V, I_{D} = 45 A,$ $_{3} = 10 V$ <b>laximum Rating</b> prward Current rd Current	(Not	-	           	510 135 22 232 224 246 72 13 31	670 176 54 474 458 502 94   45 180	PF pF ns ns ns nc nC nC nC A A



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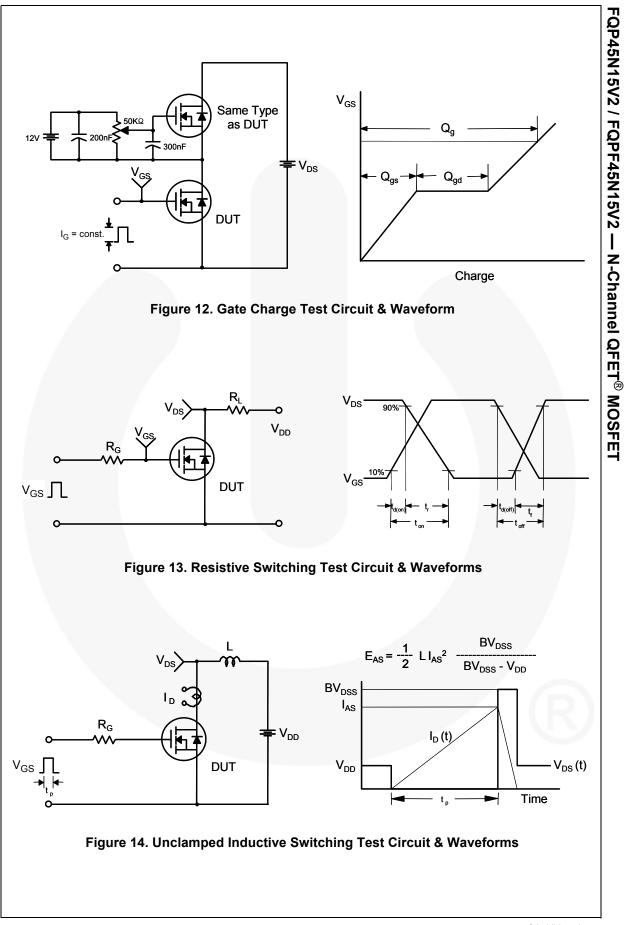


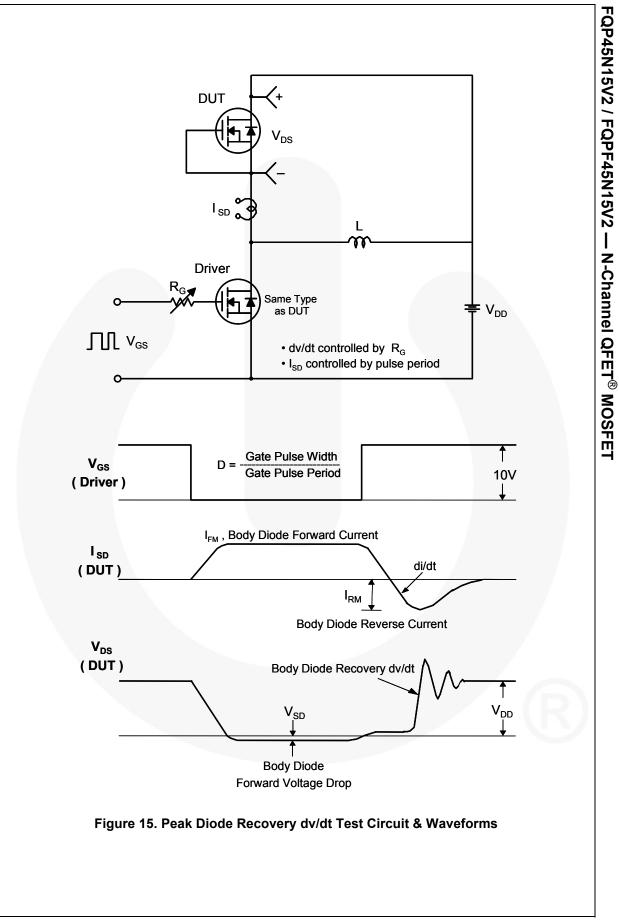
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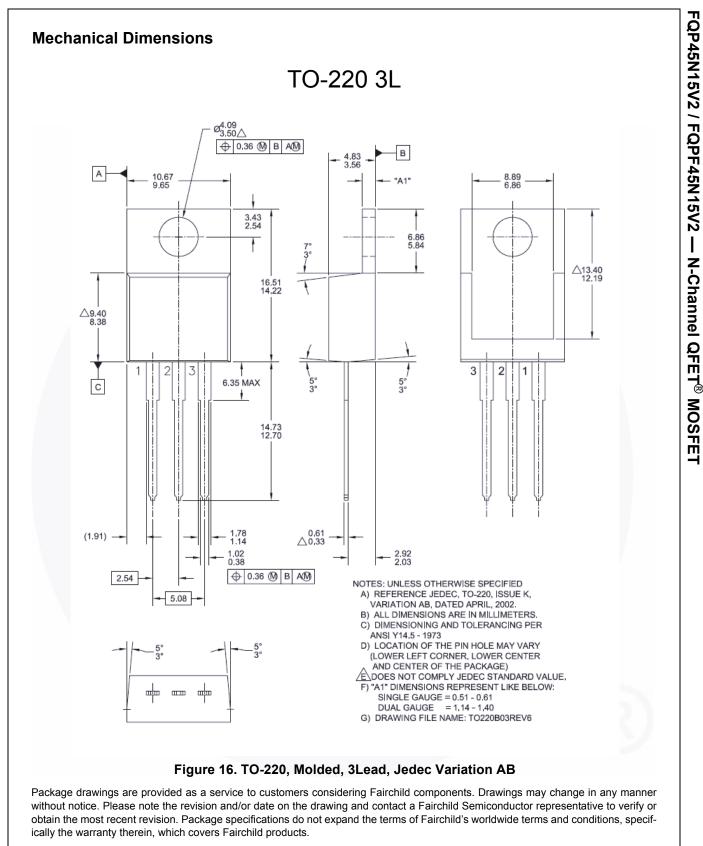


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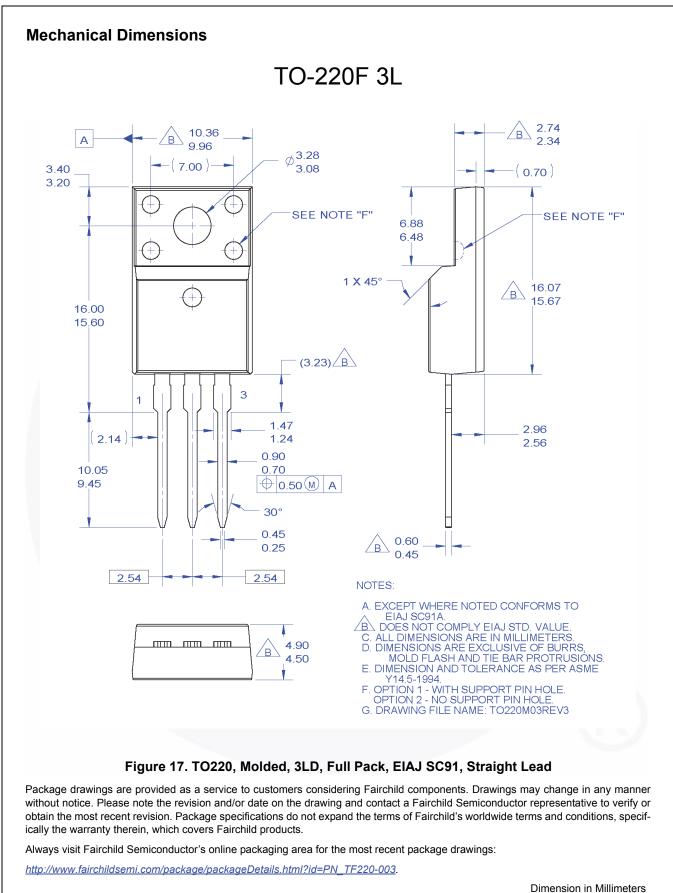




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**Dimension in Millimeters** 



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